Data Sheet | July 1999 | FN4628.1

Radiation Hardened Octal Transparent Latch, Three-State

Intersil's Satellite Applications Flow™ (SAF) devices are fully tested and guaranteed to 100kRAD total dose. These QML Class T devices are processed to a standard flow intended to meet the cost and shorter lead-time needs of large volume satellite manufacturers, while maintaining a high level of reliability.

The Intersil HCTS373T is a Radiation Hardened Octal Transparent Three-State Latch with an active-low output enable. The outputs are transparent to the inputs when the Latch Enable ($\overline{LE}$) is HIGH. When the Latch Enable ($\overline{LE}$) goes LOW, the data is latched. The Output Enable ($\overline{OE}$) controls the three-state outputs. When the Output Enable ($\overline{OE}$) is HIGH, the outputs are in the high impedance state. The latch operation is independent of the state of the Output Enable.

Specifications

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the HCTS373T are contained in SMD 5962-95747. A "hot-link" is provided from our website for downloading**.**
www.intersil.com/spacedefense/newsafclasst.asp

Intersil's Quality Management Plan (QM Plan), listing all Class T screening operations, is also available on our website.
www.intersil.com/quality/manuals.asp

Ordering Information

ORDERING NUMBER	PART NUMBER	TEMP. RANGE (^oC)
5962R9574701TRC	HCTS373DTR	-55 to 125
5962R9574701TXC	HCTS373KTR	-55 to 125

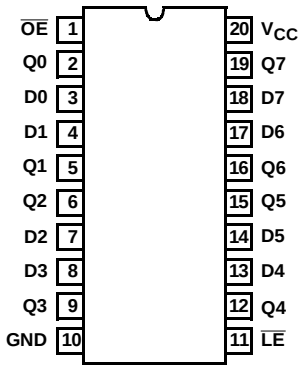
NOTE: ***Minimum order quantity for -T is 150 units through distribution, or 450 units direct.***

Features

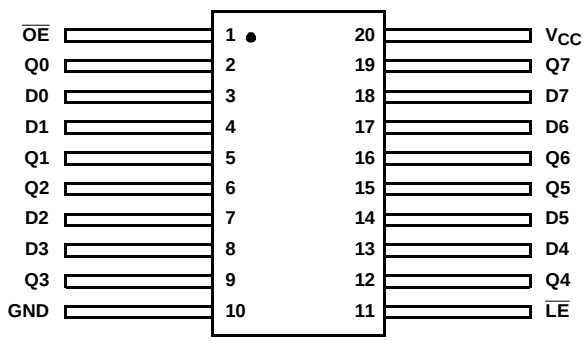
- QML Class T, Per MIL-PRF-38535
- Radiation Performance
  - Gamma Dose (γ) 1 x 10^5 RAD(Si)
  - Latch-Up Free Under Any Conditions
  - SEP Effective LET No Upsets: >100 MEV-cm^2/mg
  - Single Event Upset (SEU) Immunity < 2 x 10^{-9} Errors/Bit-Day (Typ)
- 3 Micron Radiation Hardened CMOS SOS
- Fanout (Over Temperature Range)
  - Bus Driver Outputs - 15 LSTTL Loads
- Significant Power Reduction Compared to LSTTL ICs
- DC Operating Voltage Range: 4.5V to 5.5V
- LSTTL Input Compatibility
  - V_{IL} = 0.8V Max
  - V_{IH} = $V_{CC/2}$ Min
- Input Current Levels Ii ≤ 5mA at V_{OL}, V_{OH}

Pinouts

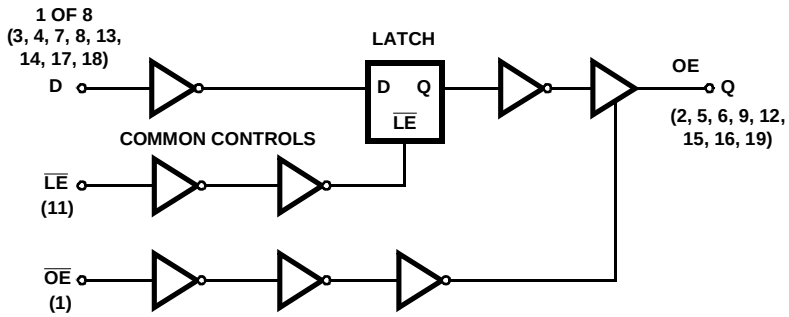
HCTS373T (SBDIP), CDIP2-T20
TOP VIEW



HCTS373T (FLATPACK), CDFP4-F20
TOP VIEW



Functional Diagram



TRUTH TABLE

$\overline{OE}$	$\overline{LE}$	D	Q
L	H	H	H
L	H	L	L
L	L	I	L
L	L	h	H
H	X	X	Z

H = High Level, L = Low Level.

X = Immaterial, Z = High Impedance.

I = Low voltage level prior to the high-to-low latch enable transition.

h = High voltage level prior to the high-to-low latch enable transition.

Die Characteristics

DIE DIMENSIONS:

(2743µm x 2692µm x 533µm ±51µm)

108 x 106 x 21mils ±2mil

METALLIZATION:

Type: Al Si

Thickness: 11kÅ ±1kÅ

SUBSTRATE POTENTIAL:

Unbiased (Silicon on Sapphire)

BACKSIDE FINISH:

Sapphire

PASSIVATION:

Type: Silox (S_iO_2)

Thickness: 13kÅ ±2.6kÅ

WORST CASE CURRENT DENSITY:

< 2.0e5 A/cm^2

TRANSISTOR COUNT:

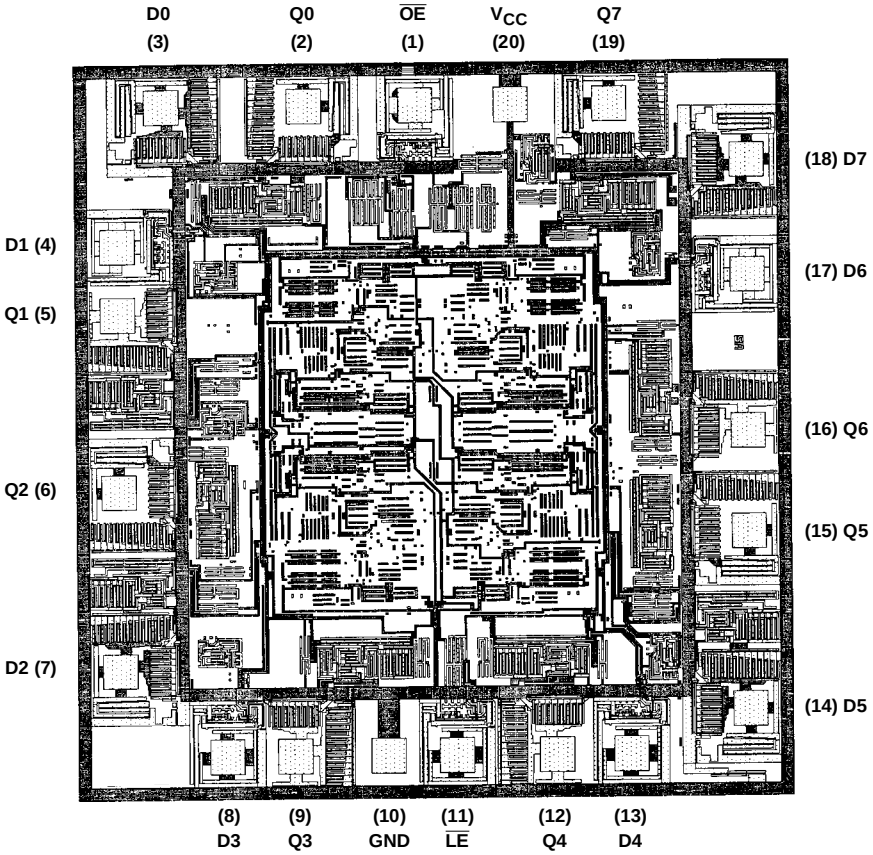
376

PROCESS:

CMOS SOS

Metallization Mask Layout

HCTS373T



NOTE: The die diagram is a generic plot from a similar HCS device. It is intended to indicate approximate die size and bond pad location. The mask series for the HCTS373 is TA14403A.